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CONFIRMATION NO. ATTORNEY DOCKET NO. APPLICATION NO. FILING DATE FIRST NAMED INVENTOR 1672 039153-0433 Craig S. Sander 10/042,732 04/25/2001 (C167596-CIP) **EXAMINER** 7590 09/03/2004 NGUYEN, THANH T Joseph N. Ziebert **FOLEY & LARDNER** ART UNIT PAPER NUMBER Firstar Center 777 East Wisconsin Avenue 2813 Milwaukee, WI 53202-5367

Please find below and/or attached an Office communication concerning this application or proceeding.

			48
Office Action Summary	Application No.	Applicant(s)	
	10/042,732	SANDER ET AL.	:
	Examiner	Art Unit	
	Thanh T. Nguyen	2813	: •
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet wit	h the correspondence addre)ss
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a re by within the statutory minimum of thirty will apply and will expire SIX (6) MONT by cause the application to become ABA	ply be timely filed (30) days will be considered timely. 'HS from the mailing date of this comm	nunication.
Status		;	:
1) Responsive to communication(s) filed on 18 J	une 2004.	-	:
2a)⊠ This action is FINAL . 2b)□ This	s action is non-final.		
3) Since this application is in condition for allowa	nce except for formal matte	ers, prosecution as to the m	erits is
closed in accordance with the practice under E	Ex parte Quayle, 1935 C.D.	11, 453 O.G. 213.	
Disposition of Claims			
4) Claim(s) 19-38 is/are pending in the applicatio	n.	:	•
4a) Of the above claim(s) is/are withdra	wn from consideration.		
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>19-38</u> is/are rejected.		• •	
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction and/o	or election requirement.		
Application Papers		:	:
9) The specification is objected to by the Examine	er.		
10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.			
Applicant may not request that any objection to the	drawing(s) be held in abeyand	e. See 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the correct	tion is required if the drawing(s	s) is objected to. See 37 CFR	1.121(d).
11)☐ The oath or declaration is objected to by the Ex	kaminer. Note the attached	Office Action or form PTO-	·152.
Priority under 35 U.S.C. § 119			
12)☐ Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. §	119(a)-(d) or (f).	
a) ☐ All b) ☐ Some * c) ☐ None of:		·	
1. Certified copies of the priority document	s have been received.		
2. Certified copies of the priority document	s have been received in Ap	plication No	
Copies of the certified copies of the prio	rity documents have been r	eceived in this National Sta	age
application from the International Burea	u (PCT Rule 17.2(a)).		
* See the attached detailed Office action for a list	of the certified copies not r	eceived.	
		:	
Attachment(s)			
1) Notice of References Cited (PTO-892)		ummary (PTO-413)	
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)		/Mail Date formal Patent Application (PTO-15	52)
 Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 	6) Other:		<i>'– ,</i>

Art Unit: 2813

DETAILED ACTION

Election/Restrictions

In view of the response to election restriction filmed on 6/18/04, the restriction has been withdrawn.

Claim Objections

Claim 19 is objected to because of the following informalities: there is a typographical error in claim 19, line 1. The term "lest" should be replace with "least". Appropriate correction is required.

In claim 20, the limitation "spacers" should be replace with "liners".

In claim 20, the limitation "a interconnect" should be replace with "an interconnect".

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Application/Control Number: 10/042,732

Art Unit: 2813

Claims 19-24 are rejected under 35 U.S.C. 102(e) as being anticipated by Fazan et al. (U.S. Patent No. 6,030,847).

Fazan et al. teaches an integrated circuit including at least one transistor, the integrated circuit comprising:

A pair of local interconnects (65) spaced from each other by a minimum lithographic feature and each being a minimum lithographic feature (see figure 5); and

A gate of the transistor (22) disposed in the space between the local interconnects and separated from of the local interconnects by an insulating liner (35, called spacer), wherein the space is less than or equal to the minimum lithographic feature, whereby the width of the transistor is not greater than three of the minimum lithographic feature (see figures 4-5).

Regarding to claim 20, wherein the insulating spacers (35) are each disposed on an interconnect wall adjacent the gate to separate each of the local interconnects from the gate (see figures 4-5).

Regarding to claim 22, the pair of local interconnect are space from each other by a minimum lithographic feature (see figures 4-5).

Regarding to claim 23, the insulating liners (35) are each disposed on an interconnect wall adjacent the gate to separate each of the local interconnects from the gate (see figures 4-5).

Regarding to claim 24, a source and drain (25/30) are disposed by at least partially beneath the insulating liner (35, see figure 5).

Application/Control Number: 10/042,732

Art Unit: 2813

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 25-38 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chung et al. (U.S. Patent No. 5,940,710) in view of Lucas et al. (U.S. Patent No. 6,287,951).

Referring to figures 2a-2e, Chung et al. teaches an integrated circuit including at least a pair of local interconnects with one interconnect on each side of gate transistor, the integrated circuit being manufactured by a method comprising the steps of:

Forming on a semiconductor substrate (1) a thick insulating layer (6);

Forming at least a pair of space apart openings (30) in the insulating layer adjacent the semiconductor substrate (1);

Forming a source (14) in one of the openings (30) and the drain (14) in one of the openings;

Filling each of the openings with a conductive material (8) to form the local interconnects (8), the local interconnect being electrically couple to the source and drain (14);

Removing a portion of the insulating layer (6) to form a gate opening between the local interconnects (8);

Forming a gate dielectric (4) on the semiconductor substrate (1) in the gate opening; and Forming the gate (5) on the gate dielectric layer.

Application/Control Number: 10/042,732

Art Unit: 2813

With regard to claims 25-26, 28-31, the terms "forming", "filling", "removing", "etch selectivity relative to" is method recitations in a device claimed, and they are non-limiting, because only the final product is relevant, not the method of making. A product by process claim is directed to the product per se, no matter how actually made. See also MPEP 2113.

Moreover, an old or obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Regarding claim 32, see figure 2e.

Regarding to claim 33, see figure 2e, col. 6, lines 10-11 (in view of the 112 rejection above).

Regarding to claims 37-38, the term "etching stop layer is formed on semiconductor substrate before forming the thick insulating layer" and "the etching selectivity" is method recitations in a device claimed, and they are non-limiting, because only the final product is relevant, not the method of making. A product by process claim is directed to the product per se, no matter how actually made. See also MPEP 2113. Moreover, an old or obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Chung et al. teaches all of the limitations as described in the claimed invention above. However, Chung et al. does not teach or suggested an etching stop layer, and forming barrier layer Titanium nitride before forming conductive material tungsten.

Lucas et al. teaches forming an etching stop layer (20/22, silicon nitride) before forming the thick insulating layer (24), forming a barrier layer titanium nitride (72) in the opening (61) and forming a conductive material tungsten (74).

Art Unit: 2813

Therefore, it would have been obvious to a person of ordinary skill in the requisite art at the time the invention was made would form an etching stop layer (silicon nitride) before forming the thick insulating layer, forming a barrier layer titanium nitride in the opening and forming a conductive material tungsten in process Chung et al. as taught by Lucas et al. because the process would prevent the chemical reaction between the conductive layer and the substrate by diffusion.

Response to Arguments

Applicant's arguments with respect to claims 19-24 have been considered but are most in view of the new ground(s) of rejection.

Applicant's arguments filed 3/3/04 have been fully considered but they are not persuasive.

Applicant contends that claims 35 recited a structure which is manufactured by a process in which holes for local interconnect are from first. In response to applicant that in regard to claims 25, the sequence of forming the structure is method recitations in a device claimed, and they are non-limiting, because only the final product is relevant, not the method of making. A product by process claim is directed to the product per se, no matter how actually made. See also MPEP 2113. Moreover, an old or obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Noted that the newly cited reference (Fazan et al. 6,030,847) also meet the limitations of claims 25-38.

Art Unit: 2813

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanh Nguyen whose telephone number is (571) 272-1695, or by Email via address Thanh Nguyen@uspto.gov. The examiner can normally be reached on Monday-Thursday from 6:00AM to 3:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead, Jr., can be reached on (571) 272-1702. The fax phone number for this Group is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-0956 (See MPEP 203.08).